

Phase Control Thyristors (Hockey PUK Version), 990 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	990 A				
V _{DRM} /V _{RRM}	800 V, 1200 V, 1400 V, 1600 V, 1800 V, 2000 V				
V _{TM}	1.62 V				
I _{GT}	100 mA				
T _J	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		990	A			
I _{T(AV)}	T _{hs}	55	°C			
1		2000	A			
I _T (RMS)	T _{hs}	25	°C			
1	50 Hz	17 800	Δ.			
I _{TSM}	60 Hz	18 700	Α			
l ² t	50 Hz	1591	kA ² s			
	60 Hz	1452	KA-S			
V _{DRM} /V _{RRM}		800 to 2000	V			
t _q	Typical	150	μs			
TJ		-40 to 125	°C			

VOLTAGE RATINGS								
TYPE VOLTAGE CODE		V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM MA				
	08	800	900					
VS-ST730CL	12	1200	1300					
	14	1400	1500	80				
	16	1600	1700	00				
	18	1800	1900					
	20	2000	2100					



ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	L	180° condu	ction, half sine	wave	990 (375)	Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	2000	
		t = 10 ms	No voltage		17 800	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		18 700	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial $T_J = T_J$ maximum	15 000	
		t = 8.3 ms	reapplied		15 700	
Maximum I ² t for fusing		t = 10 ms	140 Voltage		1591	
	l ² t	t = 8.3 ms			1452	
		t = 10 ms	100 % V _{RRM}		1125	
		t = 8.3 ms	reapplied		1027	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.98	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.32	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.27	1115.2
Maximum on-state voltage	V_{TM}	$I_{pk} = 2000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.62	V
Maximum holding current	l _Η	T 25 °C	·		600	mA
Typical latching current	l _L	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	t _q	$\begin{aligned} I_{TM} = 750 \text{ A, } T_J = T_J \text{ maximum, dI/dt} = 60 \text{ A/}\mu\text{s,} \\ V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 }\Omega, t_p = 500 \mu\text{s} \end{aligned}$	150	μs		

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
FANAIVIETEN	STWIBOL	I Ex	31 CONDITIONS	Тур.	Max.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	10.0		W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0] vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}			20		V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0	
		T _J = -40 °C	Maximum required gate trigger/	200	-	
DC gate current required to trigger	I_{GT}	T _J = 25 °C		100	200	mA
		T _J = 125 °C		50	-	
		T _J = -40 °C	current/voltage are the lowest value which will trigger all units	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}	T T managinari	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	T_{J}		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled	0.073	K/W		
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.031			
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation single side cooled	0.011	IV VV		
iviaximum thermal resistance, case to heatsink		DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)		

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL	SINUSOIDAL CONDUCTION RECTANGULAR CONDUCTION		TEST CONDITIONS	LIMITO		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum		
120°	0.011	0.011	0.010	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

Note

[•] The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

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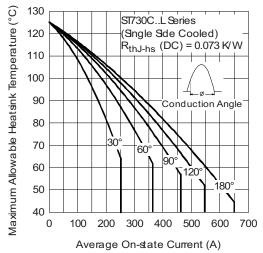


Fig. 1 - Current Ratings Characteristics

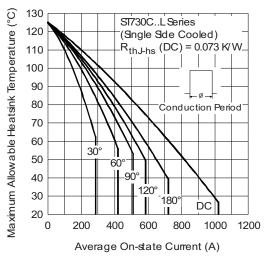


Fig. 2 - Current Ratings Characteristics

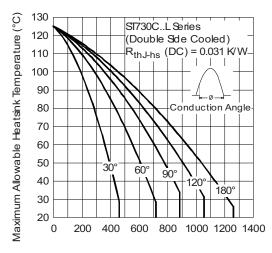


Fig. 3 - Current Ratings Characteristics

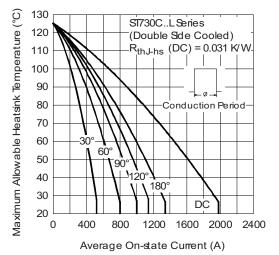


Fig. 4 - Current Ratings Characteristics

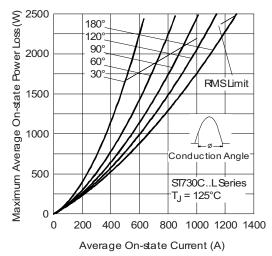


Fig. 5 - On-State Power Loss Characteristics

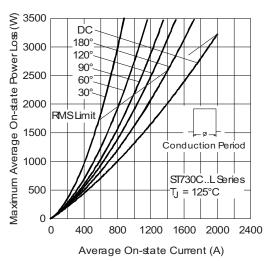
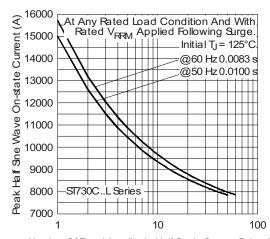


Fig. 6 - On-State Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

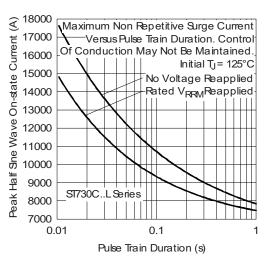


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

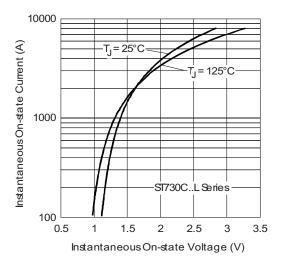


Fig. 9 - On-State Voltage Drop Characteristics

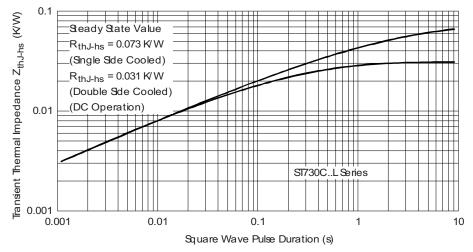


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

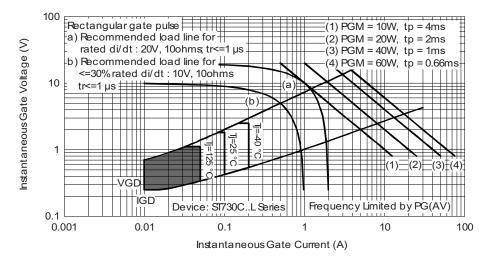


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code VS-ST 73 0 C 20 L 1 2 (3) (6) 7 (8) 4 5 9

1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

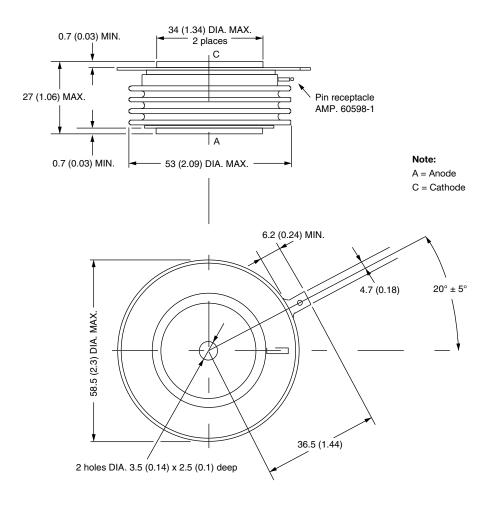
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			



B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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